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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Obsolete
Core Processor	Coldfire V2
Core Size	32-Bit Single-Core
Speed	150MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, SPI, UART/USART
Peripherals	DMA, WDT
Number of I/O	113
Program Memory Size	-
Program Memory Type	ROMIess
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.4V ~ 1.6V
Data Converters	-
Oscillator Type	External
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	256-LBGA
Supplier Device Package	256-MAPBGA (17x17)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mcf5235cvf150

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1 MCF523*x* Family Configurations

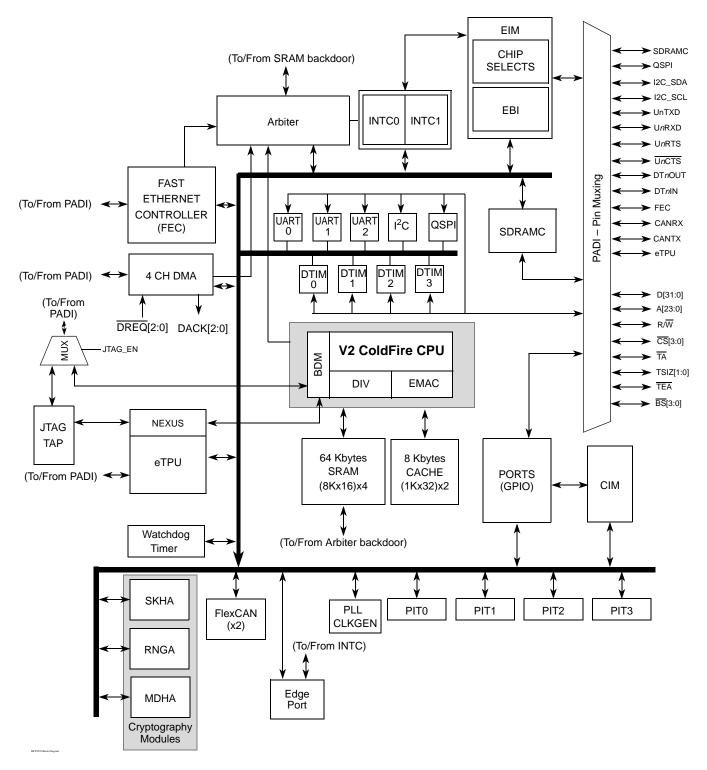
Table 1.	MCF523x	Family	Configurations
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Module	MCF5232	MCF5233	MCF5234	MCF5235
ColdFire V2 Core with EMAC (Enhanced Multiply-Accumulate Unit)	х	x	х	х
Enhanced Time Processor Unit with memory (eTPU)	16-ch 6K	32-ch 6K	16-ch 6K	32-ch 6K
System Clock		up to 1	50 MHz	
Performance (Dhrystone/2.1 MIPS)		up to	0 144	
Instruction/Data Cache		8 Kb	oytes	
Static RAM (SRAM)		64 K	bytes	
Interrupt Controllers (INTC)	2	2	2	2
Edge Port Module (EPORT)	х	х	х	х
External Interface Module (EIM)	х	х	х	х
4-channel Direct-Memory Access (DMA)	х	х	х	х
SDRAM Controller	х	х	х	х
Fast Ethernet Controller (FEC)	_	—	х	х
Cryptography - Security module for data packets processing	_	_	_	x
Watchdog Timer (WDT)	х	х	х	х
Four Periodic Interrupt Timers (PIT)	х	х	х	х
32-bit DMA Timers	4	4	4	4
QSPI	х	х	х	х
UART(s)	3	3	3	3
l ² C	х	х	х	х
FlexCAN 2.0B - Controller-Area Network communication module	1	2	1	2
General Purpose I/O Module (GPIO)	х	х	х	х
JTAG - IEEE 1149.1 Test Access Port	х	х	х	х
Package	160 QFP 196 MAPBGA	256 MAPBGA	256 MAPBGA	256 MAPBGA

2 Block Diagram

The superset device in the MCF523*x* family comes in a 256 mold array process ball grid array (MAPBGA) package. Figure shows a top-level block diagram of the MCF5235, the superset device.

Features



3 Features

For a detailed feature list see the MCF5235 Reference Manual (MCF5235RM).

Signal Descriptions

Signal Name	GPIO	Alternate 1	Alternate 2	Dir. ¹	MCF5232 160 QFP	MCF5232 196 MAPBGA	MCF5233 256 MAPBGA	MCF5234 256 MAPBGA	MCF5235 256 MAPBGA
A[20:0]	_	_	_	0	123:115, 112:106, 102:98	A12, B12, C12, A13, B13, B14, C13, C14, D12, D13, D14, E11, E12, E13, E14, F12, F13, F14, G11, G12, G13	B15, B16, C15, C16, D16, D15, D14, E16, E15, E14, E13, F15, F14, F13, G15, G14, G13, H16, H15, H14, H13	B15, B16, C15, C16, D16, D15, D14, E16, E15, E14, E13, F15, F14, F13, G15, G14, G13, H16, H15, H14, H13	B15, B16, C15, C16, D16, D15, D14, E16, E15, E14, E13, F15, F14, F13, G15, G14, G13, H16, H15, H14, H13
D[31:16]	_	_	_	0	21:24,26:30, 33:39	G1, G2, H1, H2, H3, H4, J1, J2, J3, J4, K1, K2, K3, K4, L1, L2	K1, L4, L3, L2, L1, M3, M2, M1,	K4, K3, K2, K1, L4, L3, L2, L1, M3, M2, M1, N2, N1, P2, P1, R1	K1, L4, L3, L2, L1, M3, M2, M1,
D[15:8]	PDATAH[7:0]	—	_	0	42:49,	M1, N1, M2, N2, P2, L3, M3, N3,	R2, T2, N3, P3, R3, T3, N4, P4,	R2, T2, N3, P3, R3, T3, N4, P4,	
D[7:0]	PDATAL[7:0]	_	_	0	50:52, 56:60	P3, M4, N4, P4, L5, M5, N5, P5		R4, T4, P5, R5, N6, P6, R6, N7	R4, T4, P5, R5, N6, P6, R6, N7
BS[3:0]	PBS[7:4]	CAS[3:0]	_	0	143:140	B6, C6, D7, C7	C9, B9, A9, A10	C9, B9, A9, A10	C9, B9, A9, A10
ŌE	PBUSCTL7	—	—	0	63	N6	T7	T7	T7
TA	PBUSCTL6	—	—	I	97	H11	K14	K14	K14
TEA	PBUSCTL5	DREQ1	—	Ι	—	J14	K13	K13	K13
R/W	PBUSCTL4	—	—	0	96	J13	L16	L16	L16
TSIZ1	PBUSCTL3	DACK1		0	—	P6	N8	N8	N8
TSIZ0	PBUSCTL2	DACK0	—	0	—	P7	P8	P8	P8
TS	PBUSCTL1	DACK2	—	0	—	H13	K16	K16	K16
TIP	PBUSCTL0	DREQ0		0	—	H12	K15	K15	K15
				Chip	Selects				
<u>CS</u> [7:4]	PCS[7:4]	_	_	0	_	B9, A10, C10, A11	C12, A13, C13, A14	C12, A13, C13, A14	C12, A13, C13, A14
<u>CS</u> [3:2]	PCS[3:2]	SD_CS[1:0]	—	0	134,133	A9, C9	B12, D12	B12, D12	B12, D12
CS1	PCS1	—	—	0	130	B10	B13	B13	B13
CS0	—	—	—	0	129	D10	D13	D13	D13
			SE	ORAM	Controller				

Table 2. MCF523x Signal Information and Muxing (continued)

Signal Descriptions

Table 2. MCF523x Signal Information and Muxing (continued)
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Signal Name	GPIO	Alternate 1	Alternate 2	Dir. ¹	MCF5232 160 QFP	MCF5232 196 MAPBGA	MCF5233 256 MAPBGA	MCF5234 256 MAPBGA	MCF5235 256 MAPBGA
SD_WE	PSDRAM5	_	_	0	93	K13	L13	L13	L13
SD_SCAS	PSDRAM4	_	_	0	92	K12	M15	M15	M15
SD_SRAS	PSDRAM3	_	_	0	91	K11	M14	M14	M14
SD_CKE	PSDRAM2	_	_	0		E8	C10	C10	C10
SD_CS[1:0]	PSDRAM[1:0]	_	_	0	_	L12, L13	N15, M13	N15, M13	N15, M13
			Exter	rnal In	terrupts Port	•			
IRQ[7:3]	PIRQ[7:3]	_	_	I	IRQ7=64 IRQ4=65	N7, M7, L7, P8, N8	R8, T8, N9, P9, R9	R8, T8, N9, P9, R9	R8, T8, N9, P9, R9
IRQ2	PIRQ2	DREQ2	_	I	_	M8	Т9	Т9	Т9
IRQ1	PIRQ1	_	—	I	66	L8	N10	N10	N10
			L	e	TPU	L		1	1
TPUCH31	_	ECOL	_		_		F3		F3
TPUCH30	_	ECRS	_		_	_	F4		F4
TPUCH29	_	ERXCLK			_		E3		E3
TPUCH28	_	ERXDV	_		_	_	E4		E4
TPUCH[27:24]	_	ERXD[3:0]	_		_	—	D3, D4, C3, C4	-	D3, D4, C3, C4
TPUCH23	—	ERXER	_		_	—	D5	—	D5
TPUCH22	—	ETXCLK			_	—	C5	—	C5
TPUCH21	—	ETXEN			_		D6		D6
TPUCH20	—	ETXER	_			_	C6		C6
TPUCH[19:16]	_	ETXD[3:0]	—		_	—	B6,B5, A5, B7	—	B6,B5, A5, B7
TPUCH[15:0]	_	_	_		11, 10, 7:2, 159:154, 152, 151	D2, D3, C1, C2, B1, B2,	D1, D2, C1, C2, B1, B2, A2, B3, A3,	C2, B1, B2, A2, B3, A3,	D1, D2, C1, C2, B1, B2, A2, B3, A3,
TCRCLK	PETPU2				12	E3	F1	F1	F1
UTPUODIS	PETPU1					H10	J13	J13	J13
LTPUODIS	PETPU0					G10	J14	J14	J14
				F	EC				
EMDIO	PFECI2C2	I2C_SDA	U2RXD	I/O	—	—	—	C7	C7
EMDC	PFECI2C3	I2C_SCL	U2TXD	0	_	—	—	D7	D7
ECOL	-	—	—	I	—	—	—	F3	F3

Signal Descriptions

Signal Name	GPIO	Alternate 1	Alternate 2	Dir. ¹	MCF5232 160 QFP	MCF5232 196 MAPBGA	MCF5233 256 MAPBGA	MCF5234 256 MAPBGA	MCF5235 256 MAPBGA
ECRS	_			I	_			F4	F4
ERXCLK	_			Ι	_	_		E3	E3
ERXDV	_	_	—	I	_	_	—	E4	E4
ERXD[3:0]	_	_		I				D3, D4, C3, C4	D3, D4, C3, C4
ERXER	_	—	—	I	_	—	—	D5	D5
ETXCLK	_	—	—	I		—		C5	C5
ETXEN	_	—	—	0		—		D6	D6
ETXER	_	_	—	0	_	—	—	C6	C6
ETXD[3:0]	—	—	_	0		_	_	B6, B5, A5, B7	B6, B5, A5, B7
			F	eatur	e Control	•	•		•
eTPU/EthENB		_	_	Ι		_	_	_	M4
				ļ	² C				
I2C_SDA	PFECI2C1	CANORX	_	I/O	_	J12	L15	L15	L15
I2C_SCL	PFECI2C0	CAN0TX	—	I/O	_	J11	L14	L14	L14
				D	MA				
DACK[2:0] and Please TS and DT2OL TSIZ0 and DT0 TEA and DT1II	refer to the fo JT for DACK2, OUT for DACK	llowing pins fo TSIZ1and DT (0, IRQ2 and I	or muxing: 10UT for DA DT2IN for DR	<u>CK1,</u> EQ2,	_	_	_	_	_
				Q	SPI				
QSPI_CS1	PQSPI4	SD_CKE	—	0	139	B7	B10	B10	B10
QSPI_CS0	PQSPI3	_	_	0	147	A6	D9	D9	D9
QSPI_CLK	PQSPI2	I2C_SCL	_	0	148	C5	B8	B8	B8
QSPI_DIN	PQSPI1	I2C_SDA	_	I	149	B5	C8	C8	C8
QSPI_DOUT	PQSPI0	_	_	0	150	A5	D8	D8	D8
				UA	RTs				
U2TXD	PUARTH1	CAN1TX	—	0	—	A8	D11	D11	D11
U2RXD	PUARTH0	CAN1RX	_	Ι	_	A7	D10	D10	D10
U1CTS	PUARTL7	U2CTS	—	I	—	B8	C11	C11	C11
U1RTS	PUARTL6	U2RTS	_	0	_	C8	B11	B11	B11
U1TXD	PUARTL5	CAN0TX	_	0	135	D9	A12	A12	A12

Table 2. MCF523x Signal Information and Muxing (continued)

5.2.1.2 Power Down Sequence

If V_{DD} is powered down first, then sense circuits in the I/O pads cause all output drivers to be in a high impedance state. There is no limit on how long after V_{DD} powers down before OV_{DD}/V_{DDPLL} must power down. V_{DD} should not lag OV_{DD} or V_{DDPLL} going low by more than 0.4 V during power down or there will be undesired high current in the ESD protection diodes. There are no requirements for the fall times of the power supplies.

The recommended power down sequence is as follows:

- 1. Drop V_{DD} to 0 V.
- 2. Drop OV_{DD}/V_{DDPLL} supplies.

5.3 Decoupling

- Place the decoupling caps as close to the pins as possible, but they can be outside the footprint of the package.
- 0.1 μ F and 0.01 μ F at each supply input

5.4 Buffering

• Use bus buffers on all data/address lines for all off-board accesses and for all on-board accesses when excessive loading is expected. See Section 7, "Electrical Characteristics."

5.5 Pull-up Recommendations

• Use external pull-up resistors on unused inputs. See pin table.

5.6 Clocking Recommendations

- Use a multi-layer board with a separate ground plane.
- Place the crystal and all other associated components as close to the EXTAL and XTAL (oscillator pins) as possible.
- Do not run a high frequency trace around crystal circuit.
- Ensure that the ground for the bypass capacitors is connected to a solid ground trace.
- Tie the ground trace to the ground pin nearest EXTAL and XTAL. This prevents large loop currents in the vicinity of the crystal.
- Tie the ground pin to the most solid ground in the system.
- Do not connect the trace that connects the oscillator and the ground plane to any other circuit element. This tends to make the oscillator unstable.
- Tie XTAL to ground when an external oscillator is clocking the device.

5.7 Interface Recommendations

5.7.1 SDRAM Controller

5.7.1.1 SDRAM Controller Signals in Synchronous Mode

Table 3 shows the behavior of SDRAM signals in synchronous mode.

Signal	Description
SD_SRAS	Synchronous row address strobe. Indicates a valid SDRAM row address is present and can be latched by the SDRAM. SD_SRAS should be connected to the corresponding SDRAM SD_SRAS. Do not confuse SD_SRAS with the DRAM controller's SD_CS[1:0], which should not be interfaced to the SDRAM SD_SRAS signals.
SD_SCAS	Synchronous column address strobe. Indicates a valid column address is present and can be latched by the SDRAM. SD_SCAS should be connected to the corresponding signal labeled SD_SCAS on the SDRAM.
DRAMW	DRAM read/write. Asserted for write operations and negated for read operations.
SD_CS[1:0]	Row address strobe. Select each memory block of SDRAMs connected to the MCF523 x . One SD_CS signal selects one SDRAM block and connects to the corresponding \overline{CS} signals.
SD_CKE	Synchronous DRAM clock enable. Connected directly to the CKE (clock enable) signal of SDRAMs. Enables and disables the clock internal to SDRAM. When CKE is low, memory can enter a power-down mode where operations are suspended or they can enter self-refresh mode. SD_CKE functionality is controlled by DCR[COC]. For designs using external multiplexing, setting COC allows SD_CKE to provide command-bit functionality.
BS[3:0]	Column address strobe. For synchronous operation, $\overline{\text{BS}}$ [3:0] function as byte enables to the SDRAMs. They connect to the DQM signals (or mask qualifiers) of the SDRAMs.
CLKOUT	Bus clock output. Connects to the CLK input of SDRAMs.

5.7.1.2 Address Multiplexing

See the SDRAM controller module chapter in the *MCF5235 Reference Manual* for details on address multiplexing.

5.7.2 Ethernet PHY Transceiver Connection

The FEC supports both an MII interface for 10/100 Mbps Ethernet and a seven-wire serial interface for 10 Mbps Ethernet. The interface mode is selected by R_CNTRL[MII_MODE]. In MII mode, the 802.3 standard defines and the FEC module supports 18 signals. These are shown in Table 4.

Signal Description	MCF523 <i>x</i> Pin
Transmit clock	ETXCLK
Transmit enable	ETXEN
Transmit data	ETXD[3:0]

Table 4. MII Mode

Mechanicals/Pinouts and Part Numbers

6.4 Package Dimensions—160 QFP

Figure 9 shows MCF5232CAB80 package dimensions.

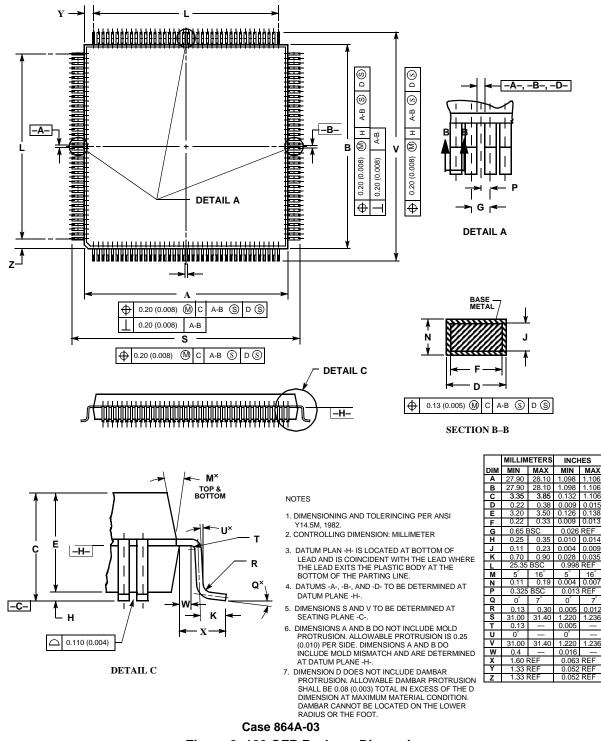


Figure 9. 160 QFP Package Dimensions

6.5 Ordering Information

Freescale Part Number	Description	Package	Speed	Lead-Free?	Temperature
MCF5232CAB80	MCF5232 RISC Microprocessor	160 QFP	80MHz	Yes	-40° to $+85^{\circ}$ C
MCF5232CVM100	MCF5232 RISC Microprocessor	196 MAPBGA	100MHz	Yes	-40° to +85° C
MCF5232CVM150	MCF5232 RISC Microprocessor	196 MAPBGA	150MHz	Yes	-40° to +85 $^{\circ}$ C
MCF5233CVM100	MCF5233 RISC Microprocessor	256 MAPBGA	100MHz	Yes	-40° to +85° C
MCF5233CVM150	MCF5233 RISC Microprocessor	256 MAPBGA	150MHz	Yes	-40° to +85 $^{\circ}$ C
MCF5234CVM100	MCF5234 RISC Microprocessor	256 MAPBGA	100MHz	Yes	-40° to +85 $^{\circ}$ C
MCF5234CVM150	MCF5234 RISC Microprocessor	256 MAPBGA	150MHz	Yes	-40° to +85 $^{\circ}$ C
MCF5235CVM100	MCF5235 RISC Microprocessor	256 MAPBGA	100MHz	Yes	-40° to +85 $^{\circ}$ C
MCF5235CVM150	MCF5235 RISC Microprocessor	256 MAPBGA	150MHz	Yes	-40° to +85 $^{\circ}$ C
MCF5235CVF150	MCF5235 RISC Microprocessor,	256 MAPBGA	150MHz	No	-40° to +85 $^{\circ}$ C

7 Electrical Characteristics

This chapter contains electrical specification tables and reference timing diagrams for the MCF5235 microcontroller unit. This section contains detailed information on power considerations, DC/AC electrical characteristics, and AC timing specifications of MCF5235.

NOTE

The parameters specified in this processor document supersede any values found in the module specifications.

7.1 Maximum Ratings

Table 7. Absolute Maximum Ratings^{1, 2}

Rating	Symbol	Value	Unit
Core Supply Voltage	V _{DD}	- 0.5 to +2.0	V
Pad Supply Voltage	OV _{DD}	- 0.3 to +4.0	V
PLL Supply Voltage	V _{DDPLL}	- 0.3 to +4.0	V
Digital Input Voltage ³	V _{IN}	- 0.3 to + 4.0	V
Instantaneous Maximum Current Single pin limit (applies to all pins) ^{3,4,5}	Ι _D	25	mA
Operating Temperature Range (Packaged)	T _A (T _L - T _H)	– 40 to 85	°C
Storage Temperature Range	T _{stg}	– 65 to 150	°C

Characteristic	Symbol	Min	Typical	Мах	Unit
Input Capacitance ³ All input-only pins All input/output (three-state) pins	C _{in}		_	7 7	pF
Load Capacitance ⁴ Low drive strength High drive strength	CL			25 50	pF pF
Core Operating Supply Current ⁵ Master Mode	I _{DD}	_	135	150	mA
Pad Operating Supply Current Master Mode Low Power Modes	OI _{DD}		100 TBD	_	mA μA
DC Injection Current ^{3, 6, 7, 8} V _{NEGCLAMP} =V _{SS} - 0.3 V, V _{POSCLAMP} = V _{DD} + 0.3 Single Pin Limit Total processor Limit, Includes sum of all stressed pins	I _{IC}	-1.0 -10		1.0 10	mA mA

Table 9. DC Electrical Specifications¹ (continued)

¹ Refer to Table 10 for additional PLL specifications.

² Refer to the MCF5235 signals section for pins having weak internal pull-up devices.

³ This parameter is characterized before qualification rather than 100% tested.

⁴ pF load ratings are based on DC loading and are provided as an indication of driver strength. High speed interfaces require transmission line analysis to determine proper drive strength and termination. See <u>High Speed Signal Propagation:</u> <u>Advanced Black Magic</u> by Howard W. Johnson for design guidelines.

⁵ Current measured at maximum system clock frequency, all modules active, and default drive strength with matching load.

⁶ All functional non-supply pins are internally clamped to V_{SS} and their respective V_{DD}.

⁷ Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

⁸ Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{in} > V_{DD}$) is greater than I_{DD} , the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Insure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the processor is not consuming power. Examples are: if no system clock is present, or if clock rate is very low which would reduce overall power consumption. Also, at power-up, system clock is not present during the power-up sequence until the PLL has attained lock.

- ⁷ This specification applies to the period required for the PLL to relock after changing the MFD frequency control bits in the synthesizer control register (SYNCR).
- ⁸ Assuming a reference is available at power up, lock time is measured from the time V_{DD} and V_{DDSYN} are valid to RSTOUT negating. If the crystal oscillator is being used as the reference for the PLL, then the crystal start up time must be added to the PLL lock time to determine the total start-up time.
- ⁹ $t_{lpll} = (64 + 4 + 5 + 5 \times \tau) \times T_{ref}$, where $T_{ref} = 1/F_{ref_crystal} = 1/F_{ref_ext} = 1/F_{ref_1:1}$, and $\tau = 1.57 \times 10^{-6} \times 2(MFD + 2)$.
- ¹⁰ PLL is operating in 1:1 PLL mode.
- ¹¹ Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{sys/2}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the PLL circuitry via V_{DDSYN} and V_{SSSYN} and variation in crystal oscillator frequency increase the Cjitter percentage for a given interval.
- ¹² Values are with frequency modulation disabled. If frequency modulation is enabled, jitter is the sum of Cjitter+Cmod.
- ¹³ Modulation percentage applies over an interval of 10µs, or equivalently the modulation rate is 100KHz.
- ¹⁴ Modulation rate selected must not result in f_{sys/2} value greater than the f_{sys/2} maximum specified value. Modulation range determined by hardware design.

¹⁵ $f_{sys/2} = f_{ico} / (2 \cdot 2^{RFD})$

7.5 External Interface Timing Characteristics

Table 11 lists processor bus input timings.

NOTE

All processor bus timings are synchronous; that is, input setup/hold and output delay with respect to the rising edge of a reference clock. The reference clock is the CLKOUT output.

All other timing relationships can be derived from these values.

Characteristic ¹	Symbol	Min	Max	Unit
System bus frequency	f _{sys/2}	50	75	MHz
CLKOUT period	t _{cyc}	_	1/75	ns
Control Inputs				
Control input valid to CLKOUT high ²	t _{CVCH}	9	—	ns
BKPT valid to CLKOUT high ³	t _{BKVCH}	9		ns
CLKOUT high to control inputs invalid ²	t _{CHCII}	0		ns
CLKOUT high to asynchronous control input BKPT invalid ³	t _{BKNCH}	0		ns
Data Inputs				
Data input (D[31:0]) valid to CLKOUT high	t _{DIVCH}	4	—	ns
CLKOUT high to data input (D[31:0]) invalid	t _{CHDII}	0	_	ns
	System bus frequency CLKOUT period Control Inputs Control input valid to CLKOUT high ² BKPT valid to CLKOUT high ³ CLKOUT high to control inputs invalid ² CLKOUT high to asynchronous control input BKPT invalid ³ Data Inputs Data input (D[31:0]) valid to CLKOUT high	System bus frequency f _{sys/2} CLKOUT period t _{cyc} Control Inputs Control Inputs Control Inputs Control Inputs Control Inputs Imputs Control Input valid to CLKOUT high ² t _{CVCH} BKPT valid to CLKOUT high ³ t _{BKVCH} CLKOUT high to control inputs invalid ² t _{CHCII} CLKOUT high to asynchronous control input BKPT invalid ³ t _{BKNCH} Data Inputs Data input (D[31:0]) valid to CLKOUT high t _{DIVCH}	System bus frequency f_sys/2 50 CLKOUT period t_cyc Control Inputs Control Inputs Control Inputs Control input valid to CLKOUT high ² t_CVCH 9 BKPT valid to CLKOUT high ³ t_BKVCH 9 CLKOUT high to control inputs invalid ² t_CHCII 0 CLKOUT high to asynchronous control input BKPT invalid ³ t_BKNCH 0 Data inputs Data input (D[31:0]) valid to CLKOUT high t_DIVCH 4	System bus frequency f f f f CLKOUT period t f

Table 11. Processor Bus Input Timing Specifications

¹ Timing specifications are tested using full drive strength pad configurations in a 50ohm transmission line environment..

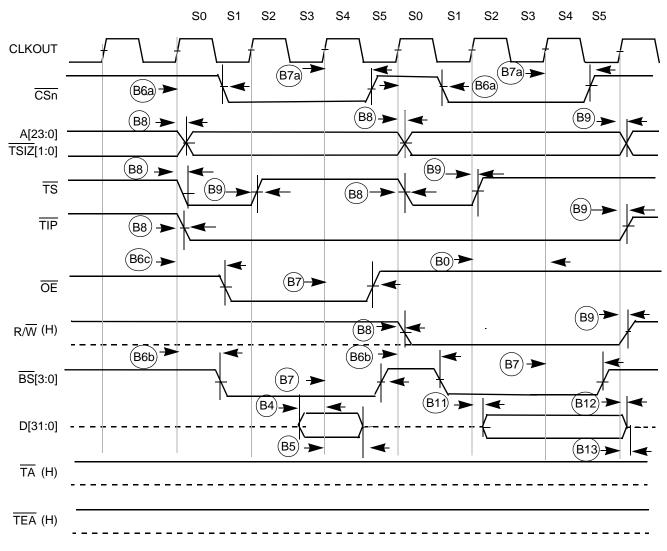
 2 TEA and TA pins are being referred to as control inputs.

³ Refer to figure A-19.

Name	Characteristic	Symbol	Min	Мах	Unit		
	Address and Attribute C	Outputs					
B8	CLKOUT high to address (A[23:0]) and control (\overline{TS} , TSIZ[1:0], TIP, R/W) valid	t _{CHAV}	—	9	ns		
B9	CLKOUT high to address (A[23:0]) and control (\overline{TS} , TSIZ[1:0], TIP, R/W) invalid	t _{CHAI}	1.5	_	ns		
	Data Outputs						
B11	CLKOUT high to data output (D[31:0]) valid	t _{CHDOV}		9	ns		
B12	CLKOUT high to data output (D[31:0]) invalid	t _{CHDOI}	1.5	—	ns		
B13	CLKOUT high to data output (D[31:0]) high impedance	t _{CHDOZ}	—	9	ns		

Table 12. External Bus Output Timing Specifications (continued)

CS transitions after the falling edge of CLKOUT.
 BS transitions after the falling edge of CLKOUT.
 OE transitions after the falling edge of CLKOUT.



Read/write bus timings listed in Table 12 are shown in Figure 11, Figure 12, and Figure 13.

Figure 11. Read/Write (Internally Terminated) SRAM Bus Timing

Figure 14 shows an SDRAM read cycle.

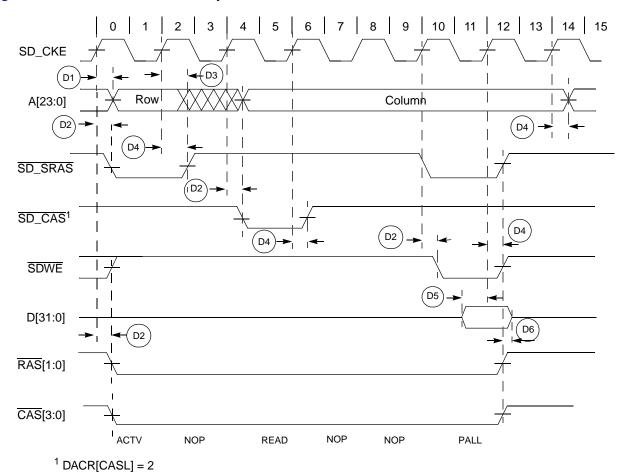


Figure	14.	SDRAM	Read	Cycle
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Table	13.	SDRAM	Timing
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NUM	Characteristic	Symbol	Min	Max	Unit
D1	CLKOUT high to SDRAM address valid	t _{CHDAV}	_	9	ns
D2	CLKOUT high to SDRAM control valid	t _{CHDCV}	_	9	ns
D3	CLKOUT high to SDRAM address invalid	t _{CHDAI}	1.5	_	ns
D4	CLKOUT high to SDRAM control invalid	t _{CHDCI}	1.5	—	ns
D5	SDRAM data valid to CLKOUT high	t _{DDVCH}	4	_	ns
D6	CLKOUT high to SDRAM data invalid	t _{CHDDI}	1.5	_	ns
D7 ¹	CLKOUT high to SDRAM data valid	t _{CHDDVW}	—	9	ns
D8 ¹	CLKOUT high to SDRAM data invalid	t _{CHDDIW}	1.5		ns

¹ D7 and D8 are for write cycles only.

7.10.2 MII Transmit Signal Timing (ETXD[3:0], ETXEN, ETXER, ETXCLK)

 Table 19 lists MII transmit channel timings.

The transmitter functions correctly up to a ETXCLK maximum frequency of 25 MHz +1%. The processor clock frequency must exceed twice the ETXCLK frequency.

Num	Characteristic	Min	Max	Unit
M5	ETXCLK to ETXD[3:0], ETXEN, ETXER invalid	5	_	ns
M6	ETXCLK to ETXD[3:0], ETXEN, ETXER valid	—	25	ns
M7	ETXCLK pulse width high	35%	65%	ETXCLK period
M8	ETXCLK pulse width low	35%	65%	ETXCLK period

Figure 20 shows MII transmit signal timings listed in Table 19.

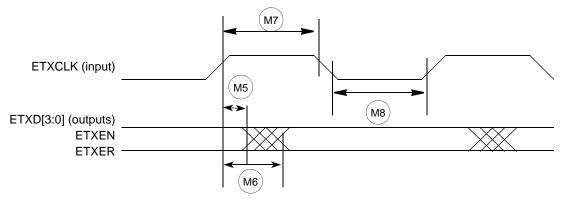


Figure 20. MII Transmit Signal Timing Diagram

7.10.3 MII Async Inputs Signal Timing (ECRS and ECOL)

Table 20 lists MII asynchronous inputs signal timing.

Table 20. MII Async Inputs Signal Timing

Ī	Num	Characteristic	Min	Мах	Unit
Ī	M9	ECRS, ECOL minimum pulse width	1.5	_	ETXCLK period

Figure 21 shows MII asynchronous input timings listed in Table 20.

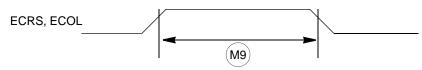


Figure 21. MII Async Inputs Timing Diagram

JTAG and Boundary Scan Timing 7.13

Table 24. JTAG and Boundary Scan Timing

CLK Frequency of Operation CLK Cycle Period CLK Clock Pulse Width CLK Rise and Fall Times oundary Scan Input Data Setup Time to TCLK Rise oundary Scan Input Data Hold Time after TCLK Rise	fJCYC tJCYC tJCW tJCRF tBSDST tBSDHT	DC 4 26 0 4 26	1/4 — — 3 —	f _{sys/2} t _{CYC} ns ns ns
CLK Clock Pulse Width CLK Rise and Fall Times pundary Scan Input Data Setup Time to TCLK Rise	t _{JCW} t _{JCRF} t _{BSDST}	26 0 4		ns ns
CLK Rise and Fall Times oundary Scan Input Data Setup Time to TCLK Rise	t _{JCRF} t _{BSDST}	0		ns
oundary Scan Input Data Setup Time to TCLK Rise	t _{BSDST}	4	3	_
			—	ns
oundary Scan Input Data Hold Time after TCLK Rise	t _{BSDHT}	26		1
	202	20	—	ns
CLK Low to Boundary Scan Output Data Valid	t _{BSDV}	0	33	ns
CLK Low to Boundary Scan Output High Z	t _{BSDZ}	0	33	ns
IS, TDI Input Data Setup Time to TCLK Rise	t _{TAPBST}	4	_	ns
/IS, TDI Input Data Hold Time after TCLK Rise	t _{TAPBHT}	10	—	ns
CLK Low to TDO Data Valid	t _{TDODV}	0	26	ns
CLK Low to TDO High Z	t _{TDODZ}	0	8	ns
RST Assert Time	t _{TRSTAT}	100	-	ns
RST Setup Time (Negation) to TCLK High	t _{TRSTST}	10	—	ns
	LK Low to Boundary Scan Output High Z IS, TDI Input Data Setup Time to TCLK Rise IS, TDI Input Data Hold Time after TCLK Rise LK Low to TDO Data Valid LK Low to TDO High Z ST Assert Time ST Setup Time (Negation) to TCLK High	LK Low to Boundary Scan Output Data Valid tBSDV LK Low to Boundary Scan Output High Z tBSDZ IS, TDI Input Data Setup Time to TCLK Rise tTAPBST IS, TDI Input Data Hold Time after TCLK Rise tTAPBHT LK Low to TDO Data Valid tTDODV LK Low to TDO High Z tTDODZ ST Assert Time tTRSTAT	LK Low to Boundary Scan Output Data Validt BSDV0LK Low to Boundary Scan Output High Zt BSDZ0IS, TDI Input Data Setup Time to TCLK Riset TAPBST4IS, TDI Input Data Hold Time after TCLK Riset TAPBHT10LK Low to TDO Data Validt TDODV0LK Low to TDO High Zt TDODZ0ST Assert Timet TRSTAT100ST Setup Time (Negation) to TCLK Hight TRSTAT10	LK Low to Boundary Scan Output Data Validt BSDV033LK Low to Boundary Scan Output High Zt BSDZ033IS, TDI Input Data Setup Time to TCLK Riset TAPBST4IS, TDI Input Data Hold Time after TCLK Riset TAPBHT10LK Low to TDO Data Validt TDODV026LK Low to TDO High Zt TDODZ08ST Assert Timet TRSTAT100ST Setup Time (Negation) to TCLK Hight TRSTST10

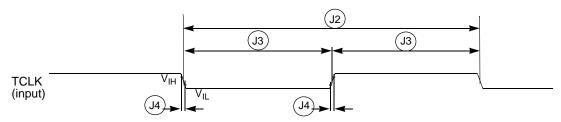


Figure 24. Test Clock Input Timing

7.14 Debug AC Timing Specifications

Table 25 lists specifications for the debug AC timing parameters shown in Figure 29.

Num	Characteristic		MHz	Units
Num	Characteristic	Min	Max	Onits
DE0	PSTCLK cycle time	_	0.5	t _{cyc}
DE1	PST valid to PSTCLK high	4	—	ns
DE2	PSTCLK high to PST invalid	1.5	_	ns
DE3	DSCLK cycle time	5	—	t _{cyc}
DE4	DSI valid to DSCLK high	1	—	t _{cyc}
DE5 ¹	DSCLK high to DSO invalid	4	—	t _{cyc}
DE6	BKPT input data setup time to CLKOUT rise	4	—	ns
DE7	CLKOUT high to BKPT high Z	0	10	ns

Table 25. Debug AC Timing Specification

¹ DSCLK and DSI are synchronized internally. D4 is measured from the synchronized DSCLK input relative to the rising edge of CLKOUT.

Figure 28 shows real-time trace timing for the values in Table 25.

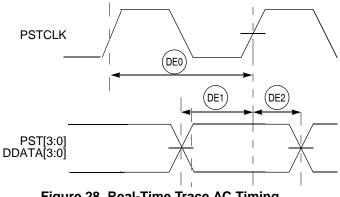


Figure 28. Real-Time Trace AC Timing

Figure 29 shows BDM serial port AC timing for the values in Table 25.

Documentation

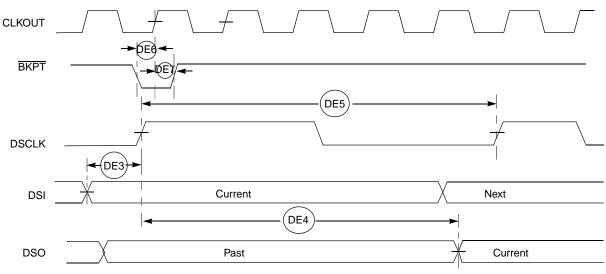


Figure 29. BDM Serial Port AC Timing

8 Documentation

Documentation regarding the MCF523x and their development support tools is available from a local Freescale distributor, a Freescale semiconductor sales office, the Freescale Literature Distribution Center, or through the Freescale web address at http://www.freescale.com/coldfire.

9 Document Revision History

The below table provides a revision history for this document.

Rev. No.	Substantive Change(s)
0	Preliminary release.
1	Updated Signal List table
1.1	Removed duplicate information in the module description sections. The information is all in the Signals Description Table.
1.2	 Corrected Figure 8 pin 81. VDD instead of VSS Changed instances of Motorola to Freescale
1.3	 Removed detailed signal description section. This information can be found in the MCF5235RM Chapter 2. Removed detailed feature list. This information can be found in the MCF5235RM Chapter 1. Corrected Figure 2 pin F10. VSS instead of VDD. Change made in Table 2 as well. Corrected Figure 8 pin 81. OVDD instead of VDD. Change made in Table 2 as well. Cleaned up many inconsistencies within the pinout figure signal names Corrected document IDs in Documentation Table
1.4	 Added values for 'Maximum operating junction temperature' in Table 8. Added typical values for 'Core operating supply current (master mode)' in Table 9. Added typical values for 'Pad operating supply current (master mode)' in Table 9. Removed unnecessary PLL specifications, #6-9, in Table 10.

Document Revision History

Rev. No.	Substantive Change(s)
1.5	 Removed Overview, Features, Modes of Operation, and Address Multiplexing sections. This information can be found in the MCF5235 Reference Manual. Removed list of documentation table in Section 8, "Documentation.". An up-to-date list is always available on our web site.
1.6	• Table 9: Changed core supply voltage (V _{DD}) from 1.35-1.65 to 1.4-1.6.
1.7	Table 10: Changed max f _{ICO} frequency from "75 MHz" to "150 MHz".
1.8	 Added Section 5.2.1, "Supply Voltage Sequencing and Separation Cautions." Updated 196MAPBGA package dimensions, Figure 3.
2	 Table 2: Changed SD_CKE pin location from 139 to "—" for the 160QFP device. Changed QSPI_CS1 pin location from "—" to 139 for the 160QFP device. Figure 8: Changed pin 139 label from "SD_CKE/QSPI_CS1" to "QSPI_CS1/SD_CKE". Removed second sentence from Section 7.10.1, "MII Receive Signal Timing (ERXD[3:0], ERXDV, ERXER, and ERXCLK)," and Section 7.10.2, "MII Transmit Signal Timing (ETXD[3:0], ETXEN, ETXER, ETXCLK)," regarding no minimum frequency requirement for TXCLK. Removed third and fourth paragraphs from Section 7.10.2, "MII Transmit Signal Timing (ETXD[3:0], ETXD[3:0], ETXEN, ETXER, ETXCLK)," as this feature is not supported on this device.
3	 Section 5.2.1, "Supply Voltage Sequencing and Separation Cautions" changed PLLV_{DD} to V_{DDPLL} to match rest of document. Section 5.2.1, "Supply Voltage Sequencing and Separation Cautions" Changed V_{DDPLL} voltage level from 1.5V to 3.3V throughout section. Section 5.2.1.1, "Power Up Sequence" first bullet, changed "Use 1 µs" to "Use 1 ms". Corrected position of spec D5 in Figure 14. Table 14: Added DACKn and DREQn to footnote. Table 9, added PLL supply voltage row
4	Added part number MCF5235CVF150 in Table 6

Table 26. MCF5235EC Revision History (continued)

Document Revision History